BLF6G10-45

Power LDMOS transistor

Rev. 02 — 20 January 2010 Product data sheet

1. Product profile

1.1 General description

45 W LDMOS power transistor for base station applications at frequencies from 700 MHz to 1000 MHz.

Table 1. Typical performance

RF performance at T_{case} = 25 °C in a common source class-AB production test circuit.

Mode of operation	f	V_{DS}	$P_{L(AV)}$	G_p	η_D	ACPR
	(MHz)	(V)	(W)	(dB)	(%)	(dBc)
2-carrier W-CDMA	920 to 960	28	1.0	22.5	7.8	–48.5[1]

[1] Test signal: 3GPP; test model 1; 64 DPCH; PAR = 7.5 dB at 0.01 % probability on CCDF per carrier; carrier spacing 5 MHz.

CAUTION

This device is sensitive to ElectroStatic Discharge (ESD). Therefore care should be taken during transport and handling.

1.2 Features

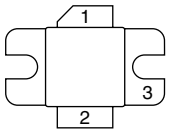
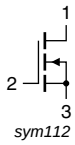
- Typical 2-carrier W-CDMA performance at frequencies of 920 MHz and 960 MHz, a supply voltage of 28 V and an I_{Dq} of 350 mA:
  - Average output power = 1.0 W
  - Gain = 22.5 dB
  - Efficiency = 7.8 %
  - ACPR = –48.5 dBc
- Easy power control
- Integrated ESD protection
- Excellent ruggedness
- High efficiency
- Excellent thermal stability
- Designed for broadband operation (700 MHz to 1000 MHz)
- Internally matched for ease of use
- Compliant to Directive 2002/95/EC, regarding restriction of hazardous substances (RoHS)

1.3 Applications

- RF power amplifiers for W-CDMA base stations and multi carrier applications in the 700 MHz to 1000 MHz frequency range.

2. Pinning information

Table 2. Pinning

Pin	Description	Simplified outline	Symbol
1	drain		
2	gate		
3	source [1]		

sym112

[1] Connected to flange.

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BLF6G10-45	-	flanged ceramic package; 2 mounting holes; 2 leads	SOT608A

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage		-	65	V
V_{GS}	gate-source voltage		−0.5	+13	V
I_D	drain current		-	13	A
T_{stg}	storage temperature		−65	+150	°C
T_j	junction temperature		-	225	°C

5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Typ	Unit
$R_{th(j\text{-}case)}$	thermal resistance from junction to case	T_{case} = 80 °C; P_L = 12.5 W	1.7	K/W

6. Characteristics

Table 6. Characteristics

T_j = 25 °C per section; unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{(BR)DSS}$	drain-source breakdown voltage	V_{GS} = 0 V; I_D = 0.5 mA	65	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	V_{DS} = 10 V; I_D = 72 mA	1.35	1.9	2.35	V
V_{GSq}	gate-source quiescent voltage	V_{DS} = 28 V; I_D = 430 mA	1.7	2.15	2.7	V
I_{DSS}	drain leakage current	V_{GS} = 0 V; V_{DS} = 28 V	-	-	1.4	μA
I_{DSX}	drain cut-off current	V_{GS} = $V_{GS(th)}$ + 3.75 V; V_{DS} = 10 V	-	12.5	-	A
I_{GSS}	gate leakage current	V_{GS} = 11 V; V_{DS} = 0 V	-	-	140	nA
g_{fs}	forward transconductance	V_{DS} = 10 V; I_D = 3.6 A	-	5	-	S
$R_{DS(on)}$	drain-source on-state resistance	V_{GS} = $V_{GS(th)}$ + 3.75 V; I_D = 2.52 A	-	0.2	-	Ω

7. Application information

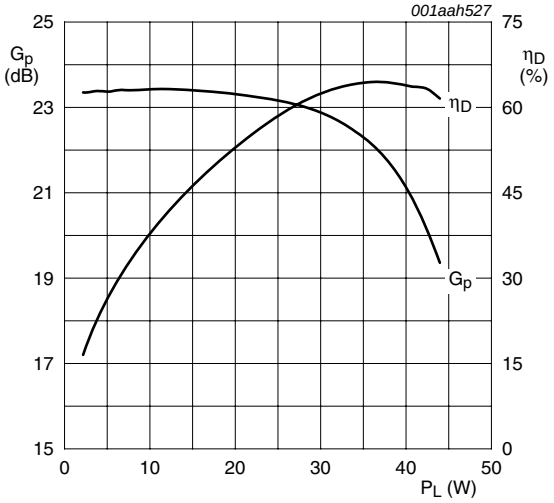
Table 7. Application information

Mode of operation: 2-carrier W-CDMA; PAR 7.5 dB at 0.01 % probability on CCDF; 3GPP test model 1; 1-64 PDPCH; f_1 = 922.5 MHz; f_2 = 927.5 MHz; f_3 = 952.5 MHz; f_4 = 957.5 MHz; RF performance at V_{DS} = 28 V; I_{Dq} = 350 mA; T_{case} = 25 °C; unless otherwise specified; in a class-AB production test circuit.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
G_p	power gain	$P_{L(AV)}$ = 1.0 W	21	22.5	23.9	dB
RL_{in}	input return loss	$P_{L(AV)}$ = 1.0 W	8	13	-	dB
η_D	drain efficiency	$P_{L(AV)}$ = 1.0 W	6.9	7.8	-	%
ACPR	adjacent channel power ratio	$P_{L(AV)}$ = 1.0 W	-	–48.5	–45.5	dBc

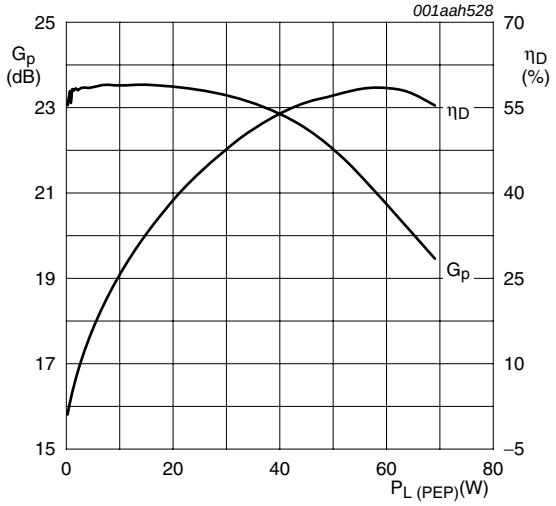
7.1 Ruggedness in class-AB operation

The BLF6G10-45 is capable of withstanding a load mismatch corresponding to VSWR = 10 : 1 through all phases under the following conditions: V_{DS} = 28 V; I_{Dq} = 350 mA; P_L = 35 W (CW); f = 960 MHz.



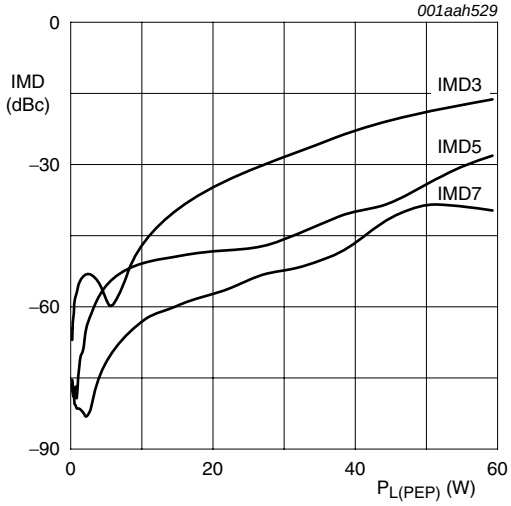
V_{DS} = 28 V; I_{Dq} = 350 mA; f = 960 MHz.

Fig 1. One-tone CW power gain and drain efficiency as functions of load power; typical values



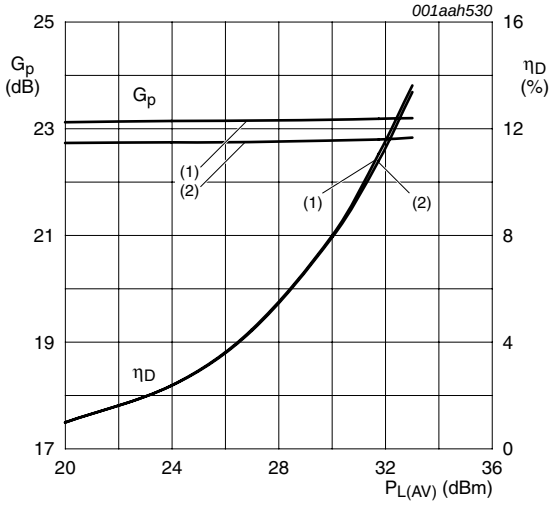
V_{DS} = 28 V; I_{Dq} = 350 mA; f_1 = 960 MHz; f_2 = 960.1 MHz.

Fig 2. Two-tone CW power gain and drain efficiency as functions of peak envelope load power; typical values



V_{DS} = 28 V; I_{Dq} = 350 mA; f_1 = 960 MHz; f_2 = 960.1 MHz.

Fig 3. Intermodulation distortion as a function of peak envelope load power; typical values

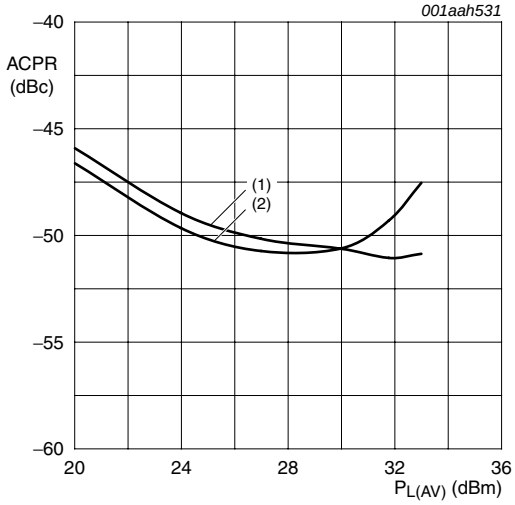


V_{DS} = 28 V; I_{Dq} = 350 mA; f_1 = 952.5 MHz; f_2 = 957.5 MHz; carrier spacing 5 MHz.

(1) f = 955 MHz.

(2) f = 925 MHz.

Fig 4. 2-carrier W-CDMA power gain and drain efficiency as functions of average load power; typical values



V_{DS} = 28 V; I_{Dq} = 350 mA; f_1 = 952.5 MHz; f_2 = 957.5 MHz; carrier spacing 5 MHz.

(1) f = 955 MHz.

(2) f = 925 MHz.

Fig 5. 2-carrier W-CDMA adjacent channel power ratio, low frequency range as functions of average load power; typical values

8. Test information

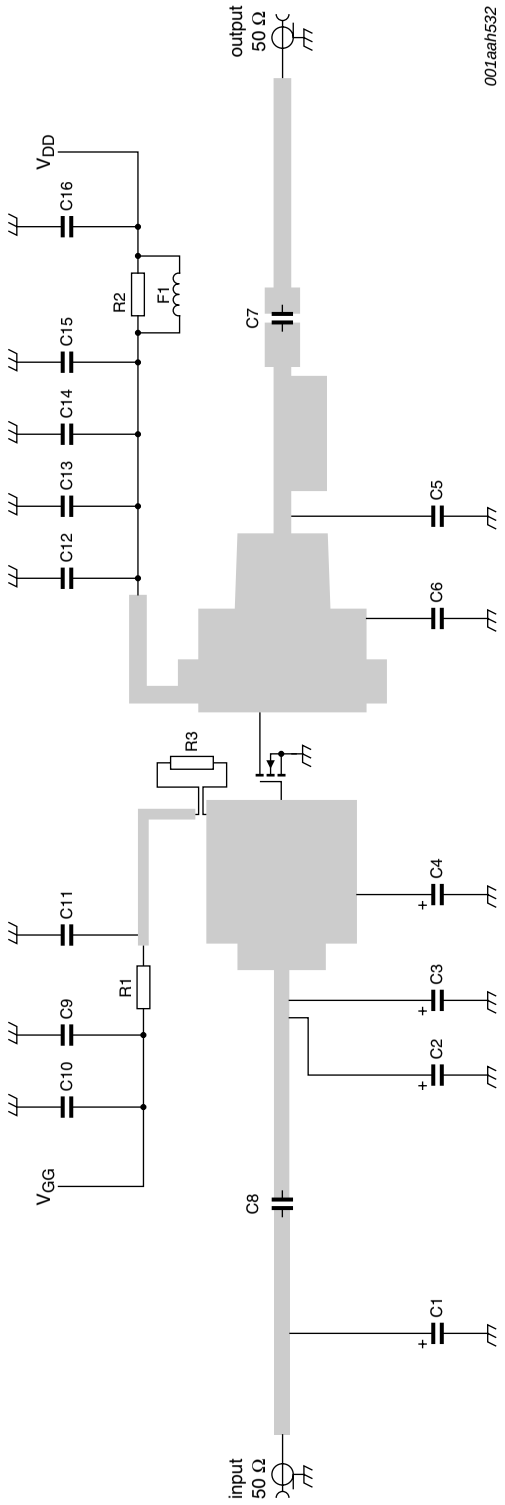
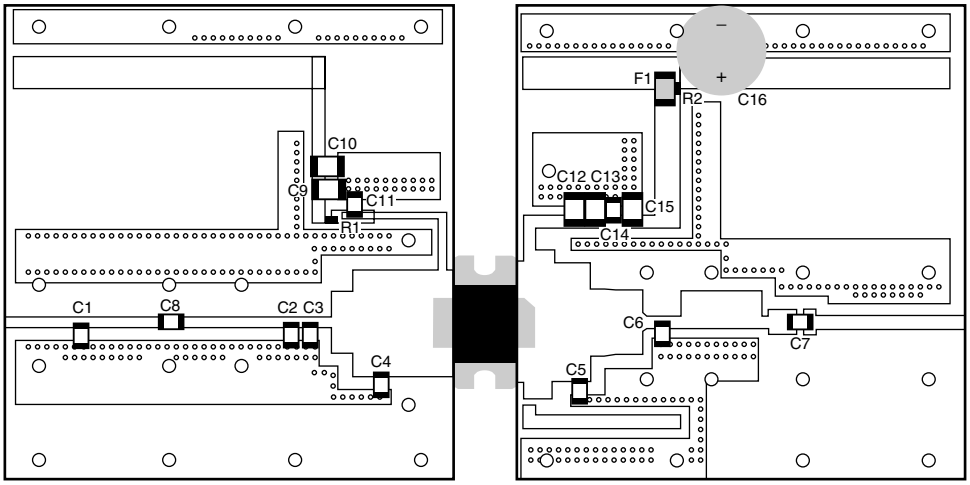


Fig 6. Test circuit for operation at 900 MHz



The striplines are on a double copper-clad Taconic RF35 Printed-Circuit Board (PCB) with ε_r = 3.5 and thickness = 0.76 mm. See Table 8 for list of components.

Fig 7. Component layout for 920 MHz and 960 MHz test circuit for 2-carrier W-CDMA

Table 8. List of components (see Figure 6 and Figure 7).

All capacitors should be soldered vertically.

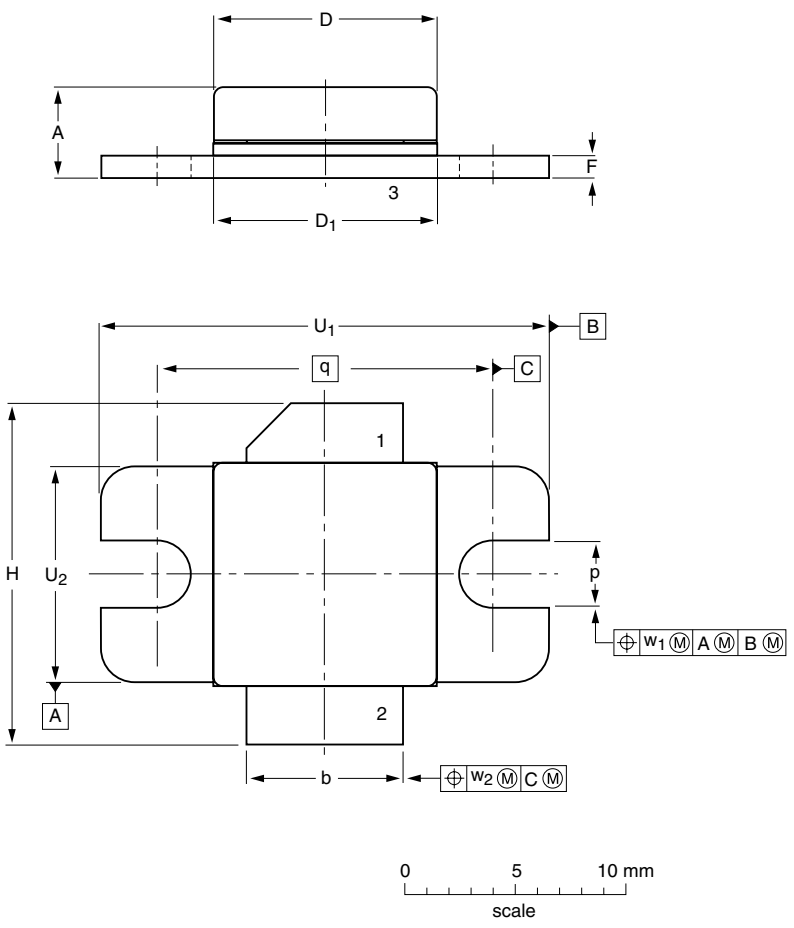
Component	Description	Value		Remarks
C1	multilayer ceramic chip capacitor	3.0 pF	[1]	
C2	multilayer ceramic chip capacitor	1 pF	[1]	
C3	multilayer ceramic chip capacitor	6.2 pF	[1]	
C4	multilayer ceramic chip capacitor	2 pF	[1]	
C5	multilayer ceramic chip capacitor	1.0 pF	[1]	
C6	multilayer ceramic chip capacitor	6.8 pF	[1]	
C7	multilayer ceramic chip capacitor	6.8 pF	[1]	
C8, C11, C14	multilayer ceramic chip capacitor	68 pF	[1]	
C9, C10, C12, C13	multilayer ceramic chip capacitor	330 nF; 50 V	[2]	
C15	multilayer ceramic chip capacitor	4.5 μF; 50 V	[2]	
C16	Electrolytic capacitor	220 μF		
F1	Ferrite SMD bead	-		Ferroxcube BDS 3/3/8.9-4S2 or equivalent
Q3	BLF6G10-45	-		
R1	SMD resistor	4.7 Ω; 0.1 W		
R2	SMD resistor	6.8 Ω; 0.1 W		

[1] American Technical Ceramics type 100B or capacitor of same quality.

[2] TDK or capacitor of same quality.

9. Package outline

Flanged ceramic package; 2 mounting holes; 2 leads **SOT608A**



DIMENSIONS (millimetre dimensions are derived from the original inch dimensions)

UNIT	A	b	c	D	D_1	E	E_1	F	H	p	Q	q	U_1	U_2	w_1	w_2
mm	4.62 3.76	7.24 6.99	0.15 0.10	10.21 10.01	10.29 10.03	10.21 10.01	10.29 10.03	1.14 0.89	15.75 14.73	3.30 2.92	1.70 1.45	15.24	20.45 20.19	9.91 9.65	0.25	0.51
inches	0.182 0.148	0.285 0.275	0.006 0.004	0.402 0.394	0.405 0.395	0.402 0.394	0.405 0.395	0.045 0.035	0.620 0.580	0.130 0.115	0.067 0.057	0.600	0.805 0.795	0.390 0.380	0.010	0.020

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT608A						~~02-02-11~~ 09-08-26

Fig 8. Package outline SOT608A

10. Abbreviations

Table 9. Abbreviations

Acronym	Description
3GPP	3rd Generation Partnership Project
CCDF	Complementary Cumulative Distribution Function
CW	Continuous Waveform
DPCH	Dedicated Physical CHannel
LDMOS	Laterally Diffused Metal Oxide Semiconductor
PAR	Peak-to-Average power Ratio
PDPCH	transmission Power of the Dedicated Physical CHannel
RF	Radio Frequency
VSWR	Voltage Standing-Wave Ratio
W-CDMA	Wideband Code Division Multiple Access

11. Revision history

Table 10. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BLF6G10-45_2	20100120	Product data sheet	-	BLF6G10-45_1
Modifications	• Section 1.1 “General description” lower frequency range extended to 700 MHz from 800 MHz. • Section 1.2 “Features” lower frequency range extended to 700 MHz from 800 MHz. • Section 1.3 “Applications” lower frequency range extended to 700 MHz from 800 MHz. • Section 12 “Legal information” export control disclaimer added.			
BLF6G10-45_1	20090203	Product data sheet	-	-

12. Legal information

12.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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14. Contents

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Date of release: 20 January 2010
Document identifier: BLF6G10-45_2